

N-Channel 100 V (D-S) Power MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I _D (A) ^a	Q _g (Typ.)			
100	85 at V _{GS} = 10 V	3.1	3.49 nC			

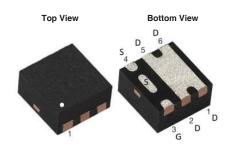
FEATURES

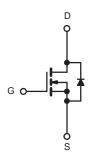
- **DT-Trench Power MOSFET**
- Low on-resistance
- SuperLow Gate Charge

APPLICATIONS

- Load Switch
- **PWM Applications**
- Power Management

DFN1.6X1.6-6L Pin Configuration





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS Parameter	(A ,	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	100			
Gate-Source Voltage	V _{GS}	± 20	V		
Continuous Drain Current (T _{.I} = 150 °C) ^a	T _A = 25 °C	1	3.1		
Continuous Diain Current (1) = 150 °C)*	T _A = 70 °C	I _D	2.5	Α	
Pulsed Drain Current ^b		I _{DM}	12		
Maximum Power Dissipation ^c	T _A = 25 °C	P _D	1.8 ^c	W	
Maximum Fower Dissipation	T _A = 70 °C	'D	1.1	VV	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	-55 to 150	°C		
Soldering Recommendations (Peak Temperature		260			

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient ^d	R _{thJA}	-	70	°C/W		

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{8JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1	-	3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μА	
	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V, T _J = 55°C	-	-	5		
On-State Drain Current a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	3.1	-	-	Α	
Durin On the On Old Brainle	В	V _{GS} = 10 V, I _D = 2 A	-	85	100	mΩ	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 2 \text{ A}$	-	110	130		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 5 \text{ V}, I_{D} = 2 \text{ A}$	-	11	-	S	
Dynamic ^b	<u>'</u>			•			
Input Capacitance	C _{iss}		-	180	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{MHz}$	-	32	-		
Reverse Transfer Capacitance	C _{rss}		-	2.5	-		
Total Gate Charge ^c	Qg		-	3.49	-	nC	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 2 \text{ A}$	-	0.66	-		
Gate-Drain Charge ^c	Q _{gd}		-	0.92	=		
Gate Resistance	R_g	f = 1 MHz	-	3.5	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	4.8	-		
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, I_D = 1 \text{ A},$	-	19	-	no	
Turn-Off Delay Time ^c	t _{d(off)}	V_{GEN} = 10 V, R_g = 3 Ω	-	17	-	ns	
Fall Time ^c	t _f		-	6	-		
Drain-Source Body Diode Ratings a	nd Characteris	stics ^b (T _C = 25 °C)					
Continuous Source Current	I _S	T _C = 25 °C	-	-	3.1	Α	
Pulsed Source Current	I _{SM}		-	-	12	Α	
Forward Voltage ^a	V _{SD}	I _F = 1 A, V _{GS} = 0 V	-	-	1.2	V	
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs	-	13	-	ns	
Reverse Recovery Charge	se Recovery Charge Q_{rr} q_{rr} q_{rr} q_{rr} q_{rr}		-	19	_	nC	

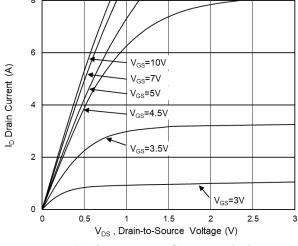
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

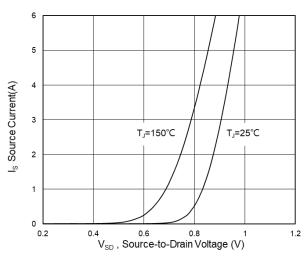
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



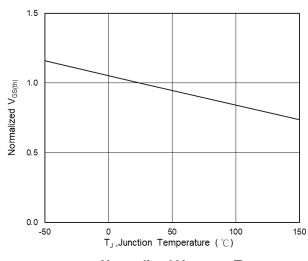
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



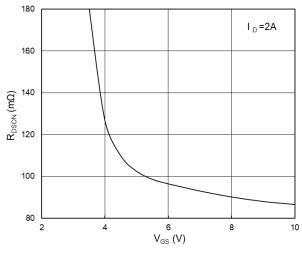
Typical Output Characteristics



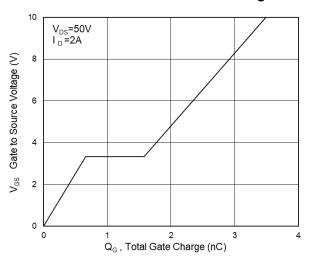
Source Drain Forward Characteristics



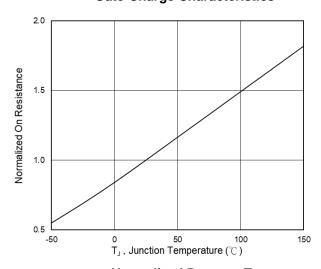
Normalized V_{GS(th)} vs T_J



On-Resistance vs G-S Voltage



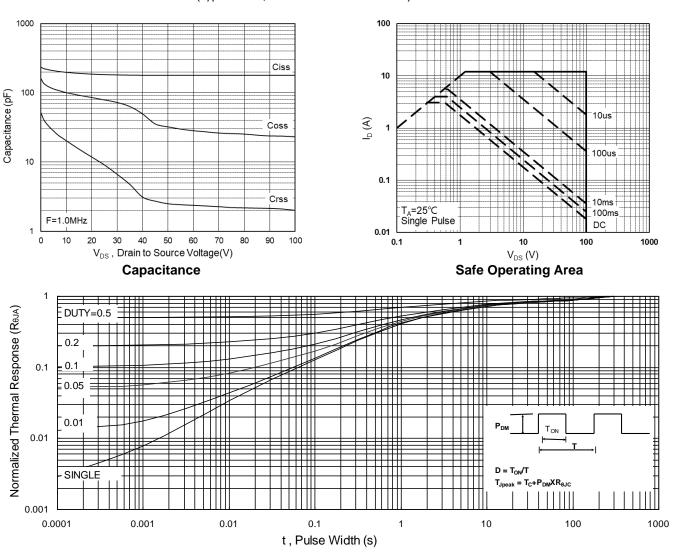
Gate-Charge Characteristics



Normalized RDSON vs TJ



TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

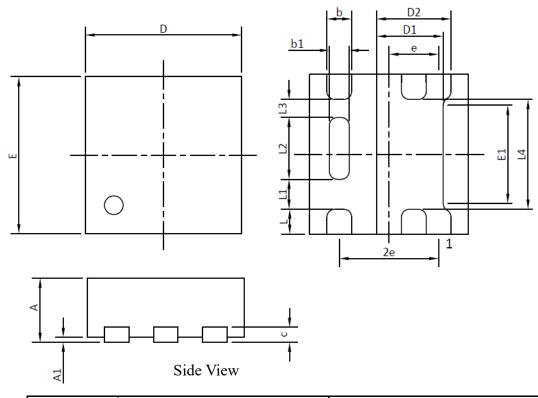


Normalized Maximum Transient Thermal Impedance



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DFN1.6*1.6-6L PACKAGE OUTLINE



SYMBOL	Millimeters			Inches			
	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.50	0.55	0.60	0.020	0.022	0.024	
A1	0.00		0.05	0.000		0.002	
b	0.22	0.25	0.28	0.009	0.010	0.011	
b1	0.17	0.20	0.23	0.007	0.008	0.009	
С	0.152 Ref.			0.006 Ref.			
D	1.55	1.60	1.65	0.061	0.063	0.065	
D1	0.67 TYP			0.026 TYP			
D2	0.75 TYP			0.030 TYP			
Е	1.55	1.60	1.65	0.061	0.063	0.065	
E1	0.98 TYP			0.039 TYP			
e	0.50 BSC			0.50 BSC 0.020 BSC			
L	0.20	0.25	0.30	0.008	0.010	0.012	
L1	0.25	0.30	0.35	0.010	0.012	0.014	
L2	0.57	0.62	0.67	0.022	0.024	0.026	
L3	0.13	0.18	0.23	0.005	0.007	0.009	
L4	1.05	1.10	1.15	0.041	0.043	0.045	





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